

TrenchHV™ Power MOSFET

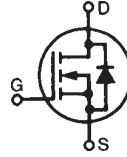
IXTH130N15T IXTQ130N15T

$$V_{DSS} = 150 \text{ V}$$

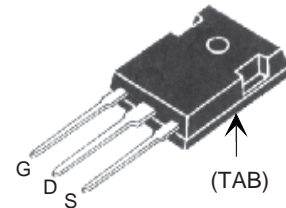
$$I_{D25} = 130 \text{ A}$$

$$R_{DS(on)} \leq 12 \text{ m}\Omega$$

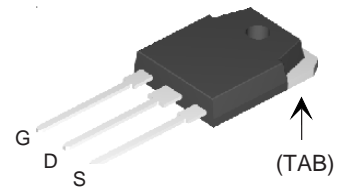
N-Channel Enhancement Mode
Avalanche Rated



TO-247 (IXTH)



TO-3P (IXTQ)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 175°C	150	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 175°C ; $R_{GS} = 1 \text{ M}\Omega$	150	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	130	A
I_{LRMS}	Lead Current Limit, RMS	75	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	330	A
I_{AR}	$T_C = 25^\circ\text{C}$	5	A
E_{AS}	$T_C = 25^\circ\text{C}$	1.2	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A/ms}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 175^\circ\text{C}$, $R_G = 2.5 \Omega$	3	V/ns
P_D	$T_C = 25^\circ\text{C}$	750	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s Plastic body for 10 seconds	300 260	$^\circ\text{C}$ $^\circ\text{C}$
M_d	Mounting torque	1.13 / 10	Nm/lb.in.
Weight	TO-3P	5.5	g
	TO-247	6	g

Features

- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect
- 175 $^\circ\text{C}$ Operating Temperature

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	150		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1 \text{ mA}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$			5 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$, Notes 1, 2	10		12 $\text{m}\Omega$

Symbol	Test Conditions	Characteristic Values			
		Min.	Typ.	Max.	
$(T_J = 25^\circ\text{C unless otherwise specified})$					
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 60\text{ A, Note 1}$	60	100		S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		9800		pF
C_{oss}			1450		pF
C_{rss}			320		pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2.5\ \Omega$ (External)		23		ns
t_r			16		ns
$t_{d(off)}$			57		ns
t_f			27		ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		113		nC
Q_{gs}			32		nC
Q_{gd}			31		nC
R_{thJC}				0.20	$^\circ\text{C/W}$
R_{thCS}		0.25			$^\circ\text{C/W}$

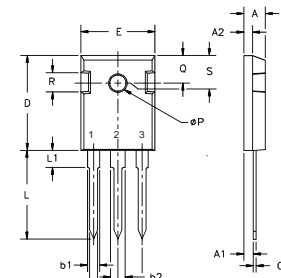
Source-Drain Diode

Symbol	Test Conditions	Characteristic Values			
		Min.	Typ.	Max.	
$T_J = 25^\circ\text{C unless otherwise specified}$					
I_S	$V_{GS} = 0\text{ V}$			130	A
I_{SM}	Pulse width limited by T_{JM}			330	A
V_{SD}	$I_F = 50\text{ A}, V_{GS} = 0\text{ V, Note 1}$			1.2	V
t_{rr}	$I_F = 50\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 25\text{ V}, V_{GS} = 0\text{ V}$		100		ns

- Notes: 1. Pulse test, $t \leq 300\text{ ms}$, duty cycle, $d \leq 2\%$;
 2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5 mm or less from the package body.

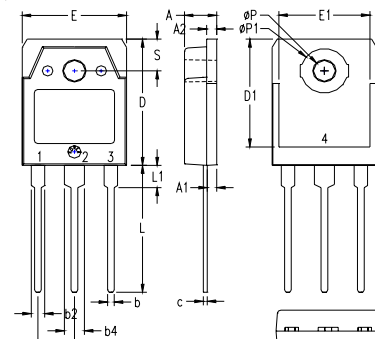
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

TO-247AD Outline


Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
∅EP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

TO-3P (IXTQ) Outline


Pins: 1 - Gate 2 - Drain
3 - Source 4, TAB - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A ₁	.051	.059	1.30	1.50
A ₂	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b ₂	.075	.087	1.90	2.20
b ₄	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.791	19.80	20.10
D ₁	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E ₁	.531	.539	13.50	13.70
e		.215 BSC		5.45 BSC
L	.779	.795	19.80	20.20
L ₁	.134	.142	3.40	3.60
∅P	.126	.134	3.20	3.40
∅P ₁	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

All metal area are tin plated.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ 25°C

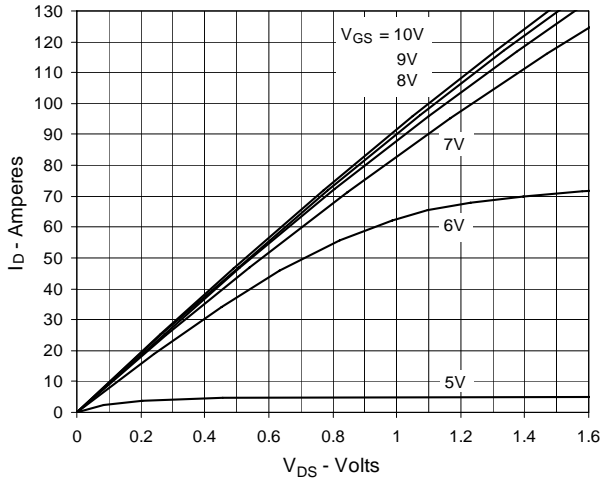


Fig. 2. Extended Output Characteristics @ 25°C

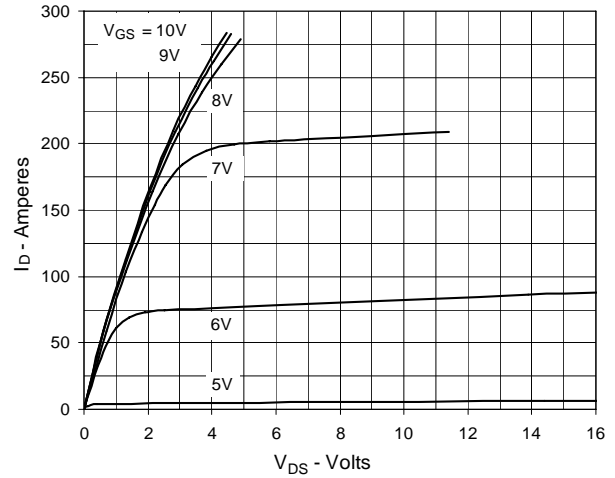


Fig. 3. Output Characteristics @ 150°C

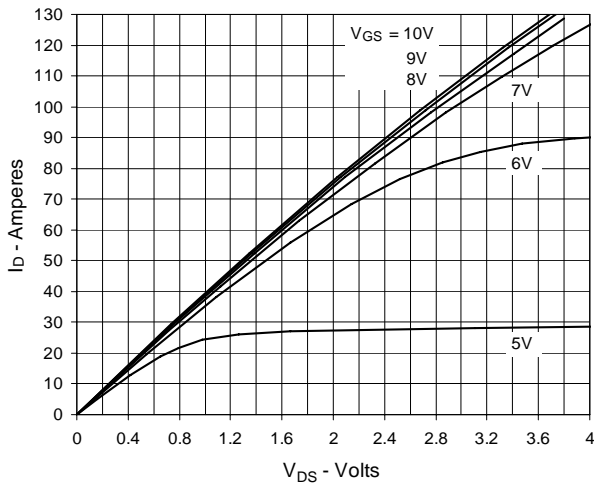


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 65A$ Value vs. Junction Temperature

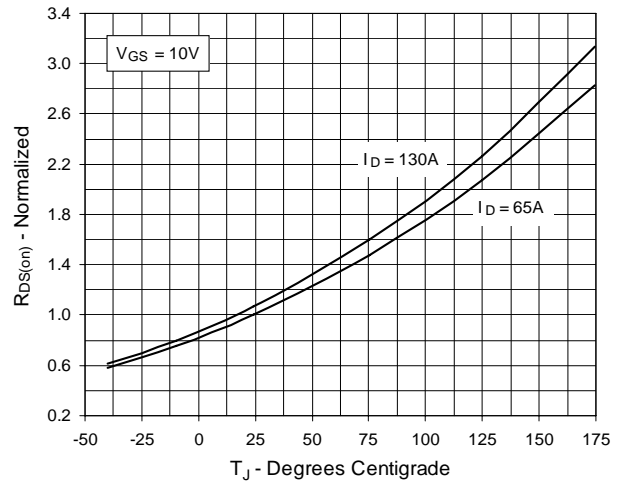


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 65A$ Value vs. Drain Current

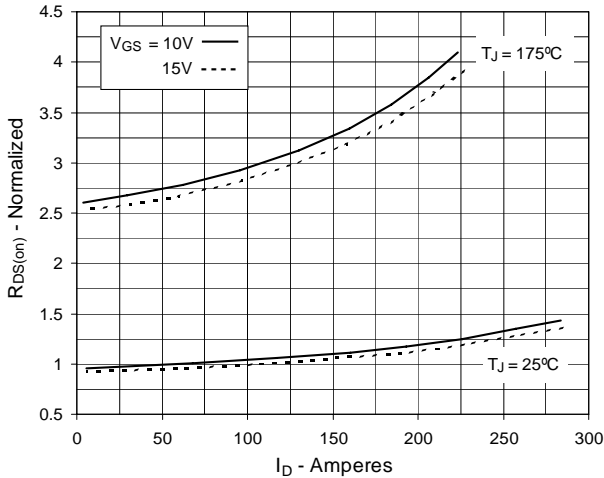


Fig. 6. Drain Current vs. Case Temperature

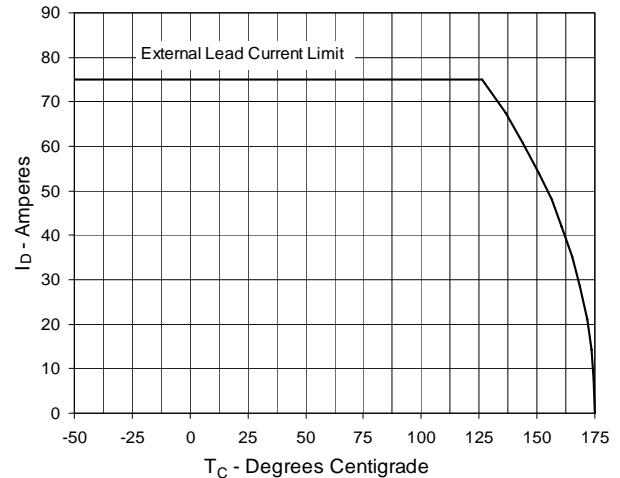


Fig. 7. Input Admittance

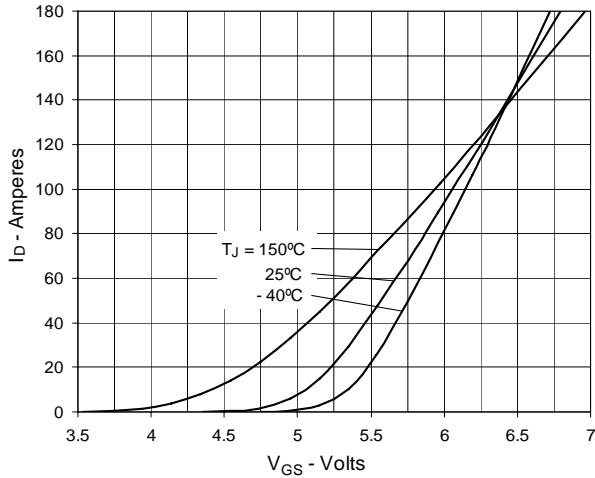


Fig. 8. Transconductance

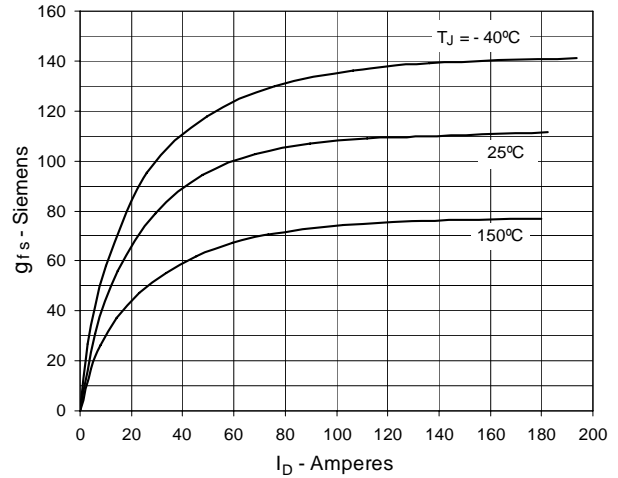


Fig. 9. Forward Voltage Drop of Intrinsic Diode

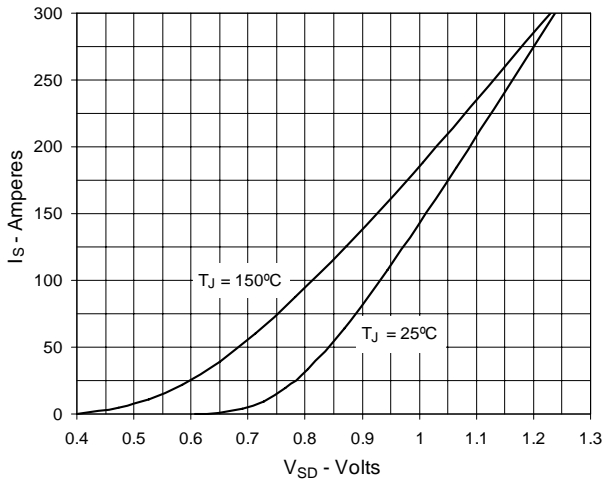


Fig. 10. Gate Charge

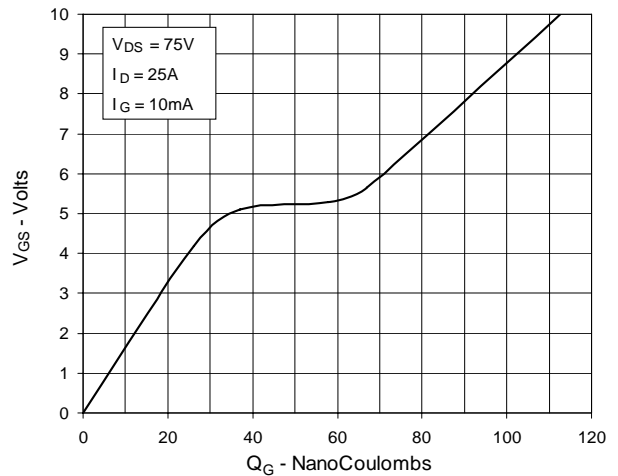


Fig. 11. Capacitance

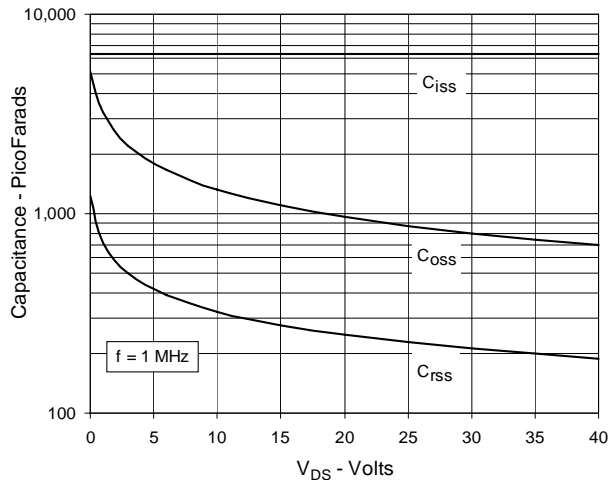
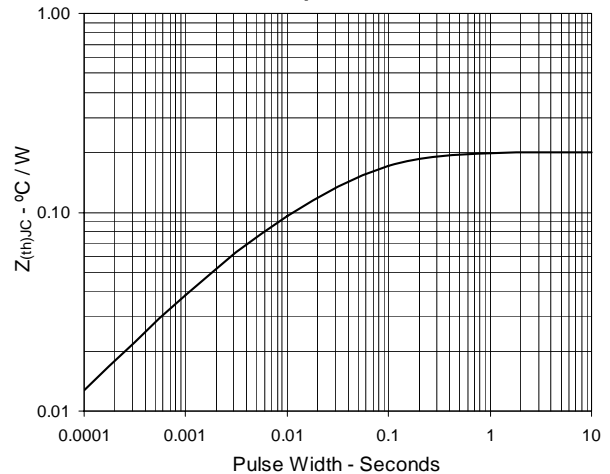
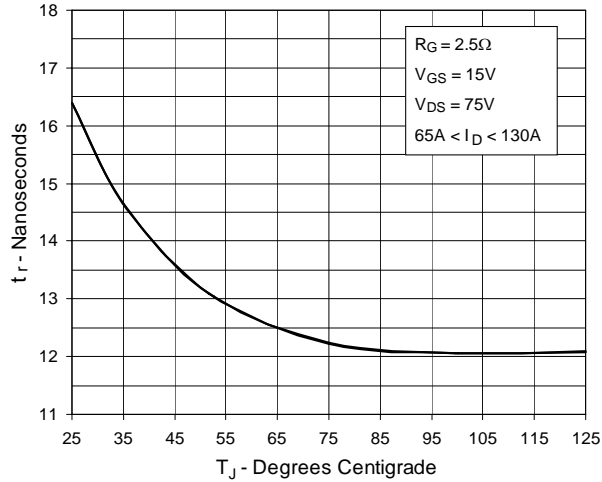


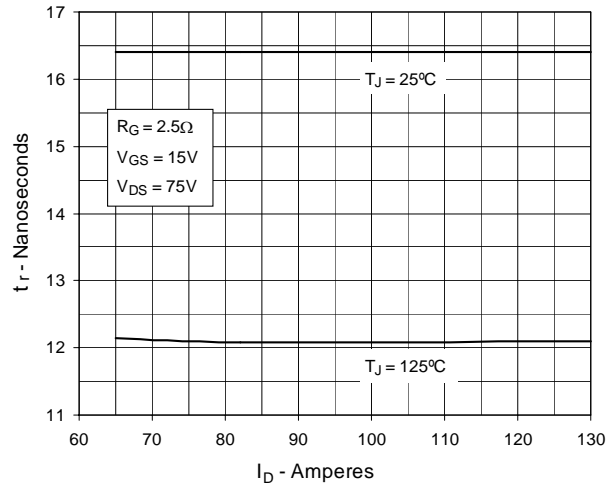
Fig. 12. Maximum Transient Thermal Impedance



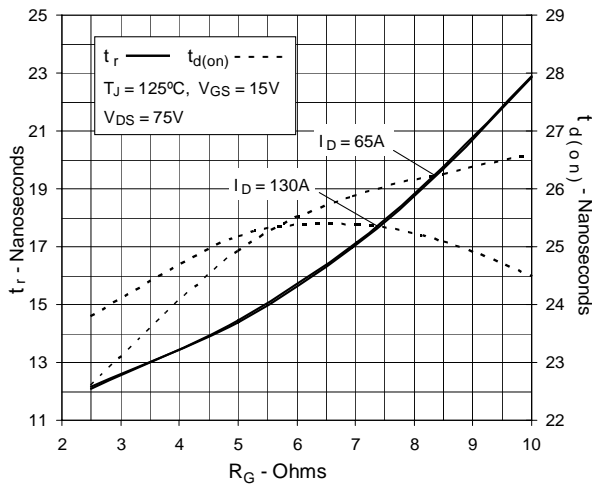
**Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature**



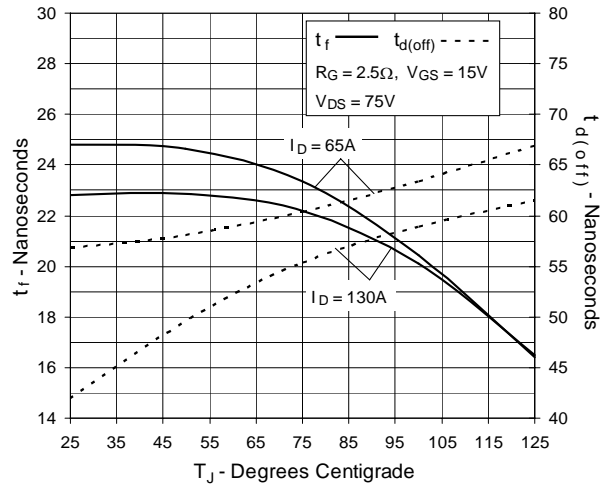
**Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current**



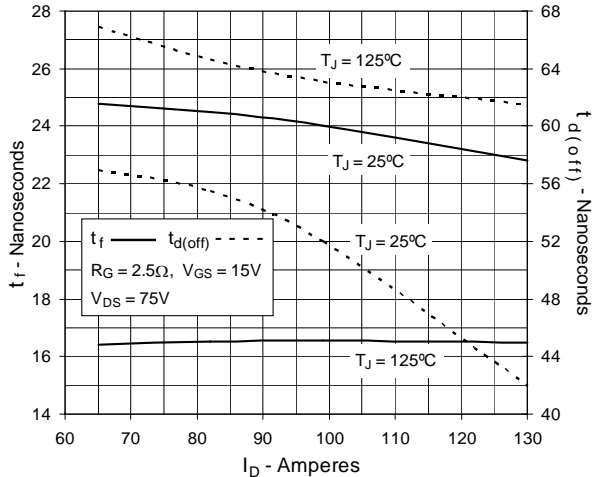
**Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance**

